

**Silicon PNP Power Transistors**

**NS50A**

**DESCRIPTION**

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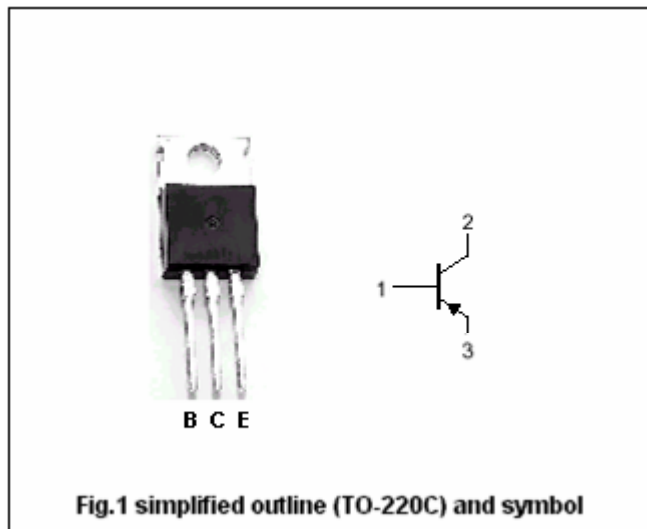
- With TO-220C package
- Complement to type NS50B

**APPLICATIONS**

- For medium power linear switching applications

**PINNING**

PIN	
1	Base
2	Collector;connected to mounting base
3	Emitter



**ABSOLUTE MAXIMUM RATINGS(T<sub>c</sub>=25 °C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current (DC)		-6	A
I <sub>CM</sub>	Collector current-Pulse		-10	A
P <sub>C</sub>	Collector power dissipation	T <sub>c</sub> =25 °C	65	W
		T <sub>a</sub> =25 °C	2	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

## Silicon PNP Power Transistors

## NS50A

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =0	-60			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-0.4A			-1.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-0.4A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-10	μA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-60V; I <sub>B</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V	100		160	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-10V	3			MHz

PACKAGE OUTLINE

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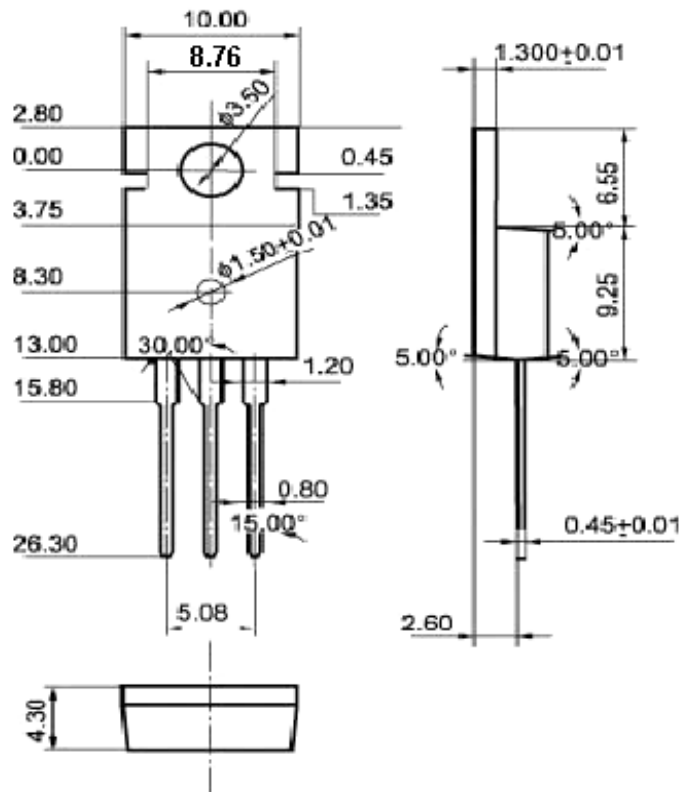


Fig.2 Outline dimensions